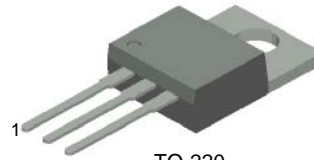




KSC5502 NPN Planar Silicon Transistor

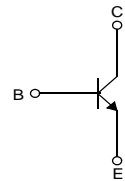
High Voltage Power Switch Mode Application

- Small Variance in Storage Time
- Wide Safe Operating Area
- Suitable for Electronic Ballast Application



1.Base 2.Collector 3.Emitter

Equivalent Circuit



Absolute Maximum Ratings * $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
BV_{CBO}	Collector-Base Voltage	1200	V
BV_{CEO}	Collector-Emitter Voltage	600	V
BV_{EBO}	Emitter-Base Voltage	12	V
I_C	Collector Current (DC)	2	A
I_{CP}	Collector Current (Pulse)**	4	A
I_B	Base Current (DC)	1	A
I_{BP}	Base Current (Pulse)**	2	A
P_C	Collector Dissipation($T_C=25^\circ\text{C}$)	50	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Junction Temperature Range	- 65 ~ 150	$^\circ\text{C}$
EAS	Avalanche Energy($T_J=25^\circ\text{C}$)	2.5	mJ

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.
 ** Pulse Test : Pulse Width = 5ms, Duty Cycle \leq 10%

Thermal Characteristics $T_a=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
$R_{\theta Jc}$	Thermal Resistance, Junction to Case	2.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	85	$^\circ\text{C/W}$

Ordering Information

Part Number	Marking	Package	Packing Method
KSC5502TU	J5502	TO-220	TUBE

Electrical Characteristics * $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units	
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C=1\text{mA}, I_E=0$	1200	1350		V	
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C=5\text{mA}, I_B=0$	600	750		V	
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E=500\mu\text{A}, I_C=0$	12	13.2		V	
I_{CES}	Collector Cut-off Current	$V_{CES}=1200\text{V}, V_{BE}=0$	$T_C=25^\circ\text{C}$			100	μA
			$T_C=125^\circ\text{C}$			500	
I_{CEO}	Collector Cut-off Current	$V_{CE}=600\text{V}, I_B=0$	$T_C=25^\circ\text{C}$			100	μA
			$T_C=125^\circ\text{C}$			500	
I_{EBO}	Emitter Cut-off Current	$V_{EB}=12\text{V}, I_C=0$			10	μA	
h_{FE}	DC Current Gain	$V_{CE}=1\text{V}, I_C=0.2\text{A}$	$T_C=25^\circ\text{C}$	15	28	40	
			$T_C=125^\circ\text{C}$	8	27		
		$V_{CE}=1\text{V}, I_C=1\text{A}$	$T_C=25^\circ\text{C}$	4	8.7		
			$T_C=125^\circ\text{C}$	3	6.6		
		$V_{CE}=2.5\text{V}, I_C=0.5\text{A}$	$T_C=25^\circ\text{C}$	12	20	30	
			$T_C=125^\circ\text{C}$	6	16		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=0.2\text{A}, I_B=0.02\text{A}$	$T_C=25^\circ\text{C}$		0.09	0.8	V
			$T_C=125^\circ\text{C}$		0.13	1.1	V
		$I_C=0.4\text{A}, I_B=0.08\text{A}$	$T_C=25^\circ\text{C}$		0.08	0.6	V
			$T_C=125^\circ\text{C}$		0.12	1.0	V
		$I_C=1\text{A}, I_B=0.2\text{A}$	$T_C=25^\circ\text{C}$		0.19	1.5	V
			$T_C=125^\circ\text{C}$		0.35	3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=0.4\text{A}, I_B=0.08\text{A}$	$T_C=25^\circ\text{C}$		0.77	1.0	V
			$T_C=125^\circ\text{C}$		0.65	0.9	V
		$I_C=1\text{A}, I_B=0.2\text{A}$	$T_C=25^\circ\text{C}$		0.83	1.2	V
			$T_C=125^\circ\text{C}$		0.70	1.0	V
C_{ib}	Input Capacitance	$V_{EB}=8\text{V}, I_C=0, f=1\text{MHz}$		410	500	pF	
C_{ob}	Output Capacitance	$V_{CB}=10\text{V}, I_E=0, f=1\text{MHz}$		20	100	pF	

* Pulse Test : Pulse Width = 5ms, Duty Cycle \leq 10%

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min	Typ.	Max.	Units	
$V_{CE(DSAT)}$	Dynamic Saturation Voltage	$I_C=0.4\text{A}, I_{B1}=80\text{mA}$ $V_{CC}=300\text{V}$	@ 1 μs	11		V	
			@ 3 μs	8		V	
		$I_C=1\text{A}, I_{B1}=200\text{mA}$ $V_{CC}=300\text{V}$	@ 1 μs	23		V	
			@ 3 μs	13		V	
RESISTIVE LOAD SWITCHING (D.C \leq 10%, Pulse Width=20s)							
t_{ON}	Turn On Time	$I_C=0.4\text{A}, I_{B1}=80\text{mA}$ $I_{B2}=0.2\text{A}, V_{CC}=300\text{V}$ $R_L = 750\Omega$	$T_C=25^\circ\text{C}$		250	350	ns
			$T_C=125^\circ\text{C}$		260		ns
t_{OFF}	Turn Off Time		$T_C=25^\circ\text{C}$		3.3	4.0	μs
			$T_C=125^\circ\text{C}$		3.8		μs
t_{ON}	Turn On Time	$I_C=1\text{A}, I_{B1}=160\text{mA}$ $I_{B2}=160\text{mA},$ $V_{CC}=300\text{V}$ $R_L = 300\Omega$	$T_C=25^\circ\text{C}$		220	450	ns
			$T_C=125^\circ\text{C}$		250		ns
t_{OFF}	Turn Off Time		$T_C=25^\circ\text{C}$		4.3	5.0	μs
			$T_C=125^\circ\text{C}$		5.0		μs
INDUCTIVE LOAD SWITCHING ($V_{CC}=15\text{V}$)							
t_{STG}	Storage Time	$I_C=0.4\text{A}, I_{B1}=80\text{mA}$ $I_{B2}=0.2\text{A}, V_Z=300\text{V}$ $L_C=200\mu\text{H}$	$T_C=25^\circ\text{C}$		1.4	2.0	μs
			$T_C=125^\circ\text{C}$		1.7		μs
t_F	Fall Time		$T_C=25^\circ\text{C}$		130	200	ns
			$T_C=125^\circ\text{C}$		80		ns
t_C	Cross-over Time	$T_C=25^\circ\text{C}$		210	350	ns	
		$T_C=125^\circ\text{C}$		130		ns	
t_{STG}	Storage Time	$I_C=0.8\text{A}, I_{B1}=160\text{mA}$ $I_{B2}=160\text{mA},$ $V_{CC}=300\text{V}$ $L_C=200\mu\text{H}$	$T_C=25^\circ\text{C}$		4.9	5.5	μs
			$T_C=125^\circ\text{C}$		5.3		μs
t_F	Fall Time		$T_C=25^\circ\text{C}$		170	250	ns
			$T_C=125^\circ\text{C}$		340		ns
t_C	Cross-over Time	$T_C=25^\circ\text{C}$		300	600	ns	
		$T_C=125^\circ\text{C}$		810		ns	

Typical Characteristics

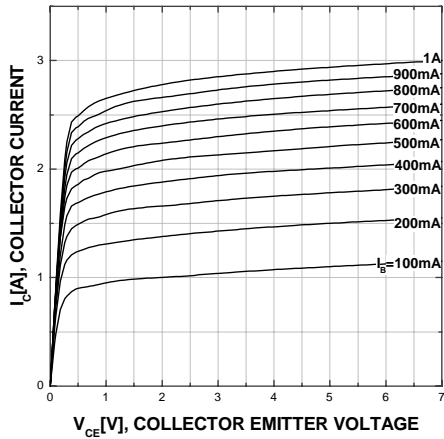


Figure 1. Static Characteristic

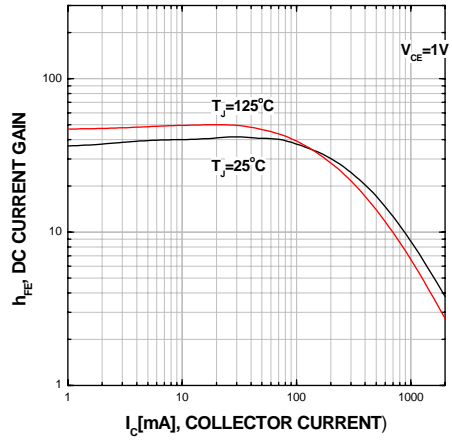


Figure 2. DC current Gain

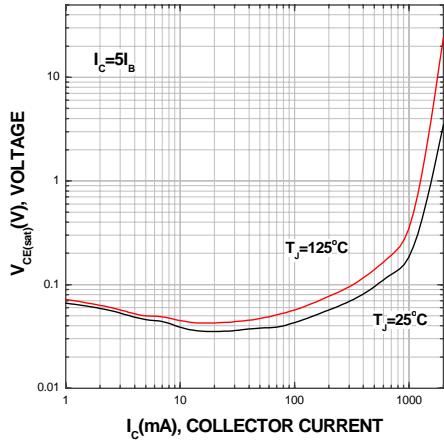


Figure 3. Collector-Emitter Saturation Voltage

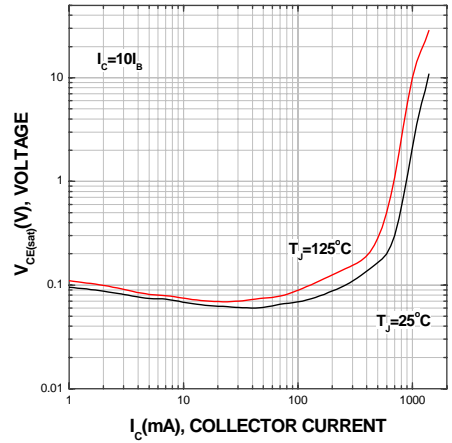


Figure 4. Collector-Emitter Saturation Voltage

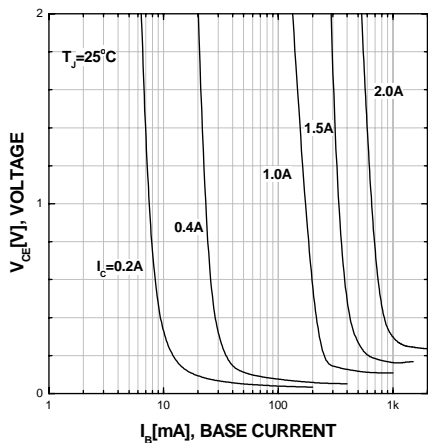


Figure 5. Typical Collector Saturation Voltage

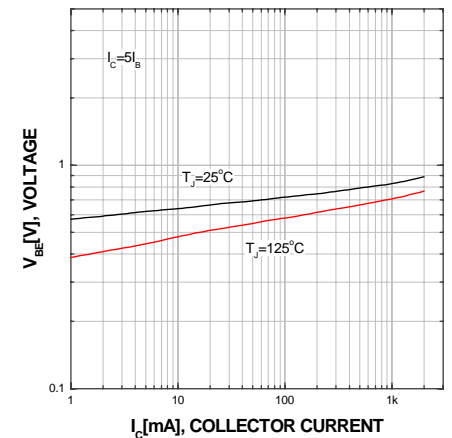


Figure 6. Base-Emitter Saturation Voltage

Typical Characteristics (Continued)

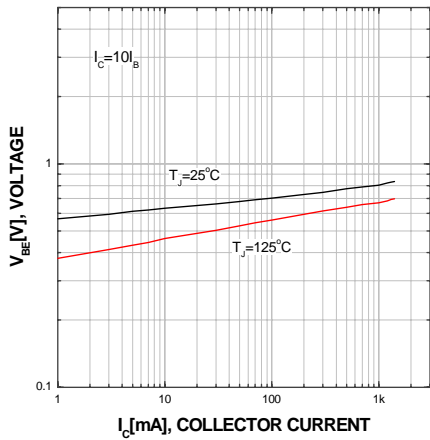


Figure 7. Base-Emitter Saturation Voltage

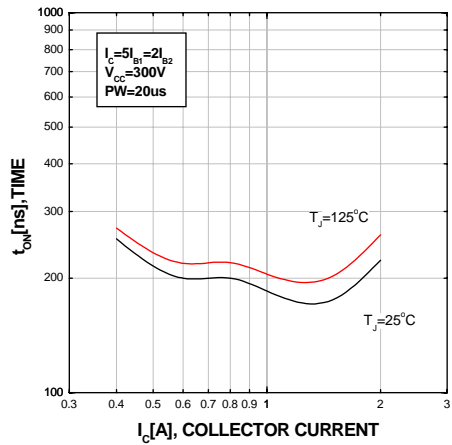


Figure 8. Resistive Switching Time, t_{on}

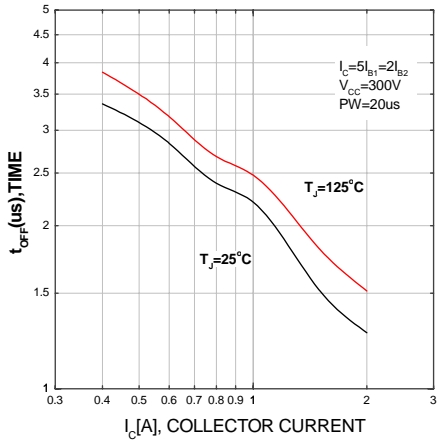


Figure 9. Resistive Switching Time, t_{off}

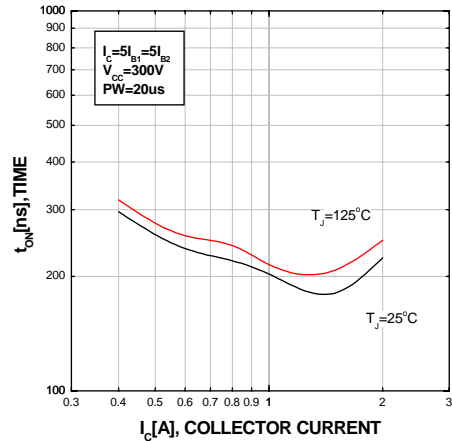


Figure 10. Resistive Switching Time, t_{on}

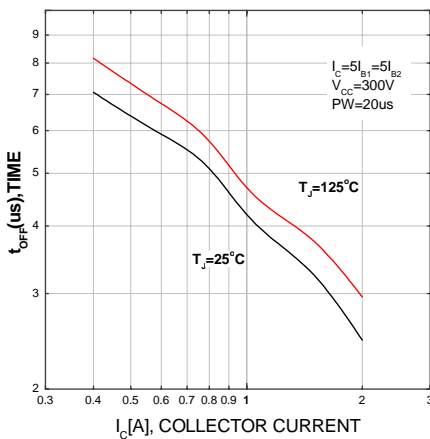


Figure 11. Resistive Switching Time, t_{off}

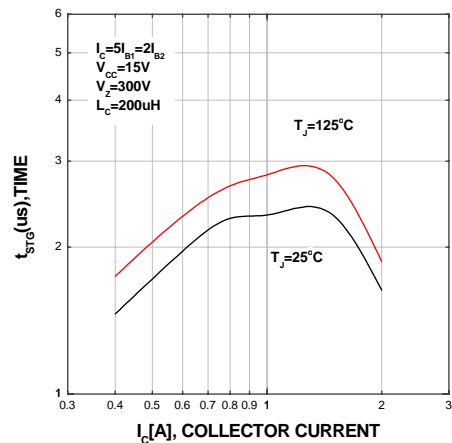


Figure 12. Inductive Switching Time, t_{STG}

Typical Characteristics (Continued)

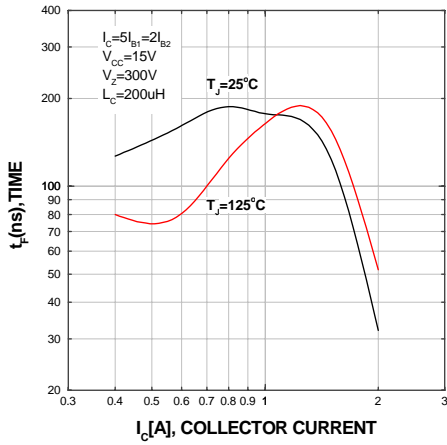


Figure 13. Inductive Switching Time, t_f

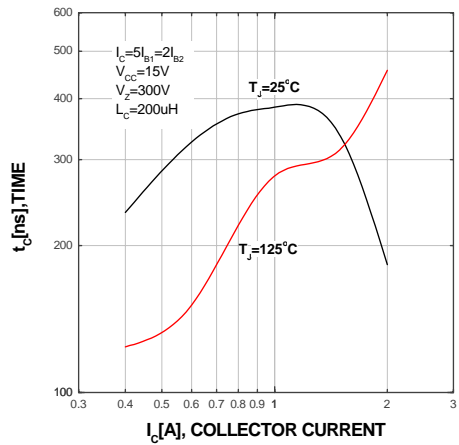


Figure 14. Inductive Switching Time, t_c

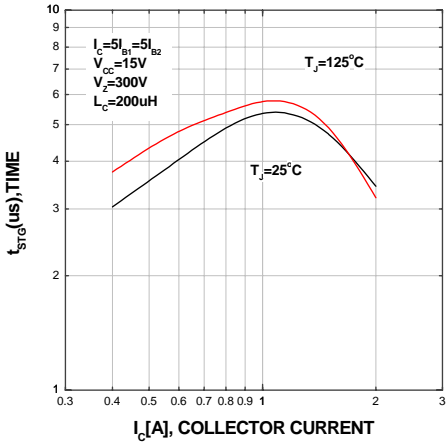


Figure 15. Inductive Switching Time, t_{STG}

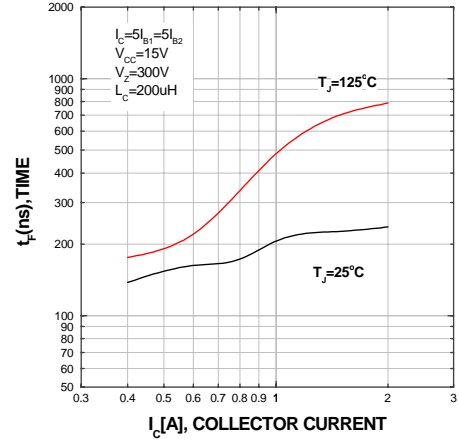


Figure 16. Inductive Switching Time, t_f

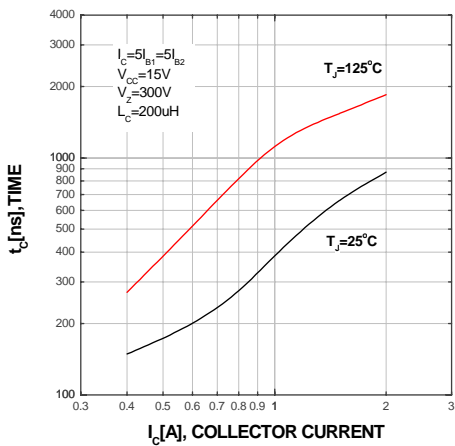


Figure 17. Inductive Switching Time, t_c

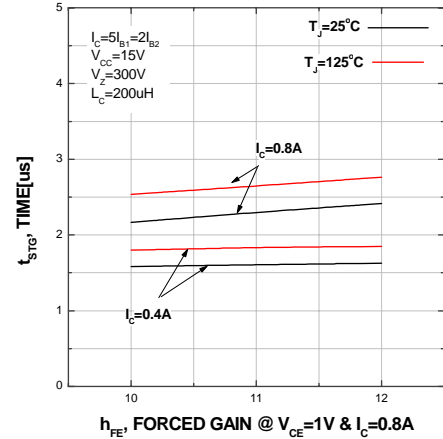


Figure 18. Inductive Switching Time, t_{STG}

Typical Characteristics (Continued)

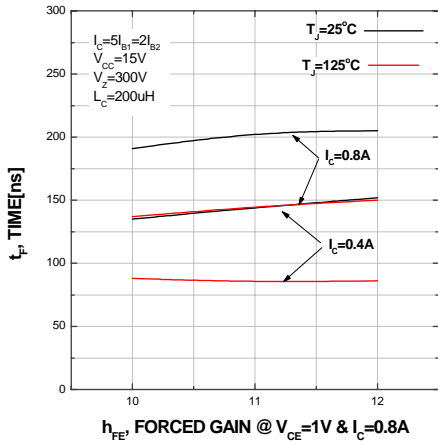


Figure 19. Inductive Switching Time, t_F

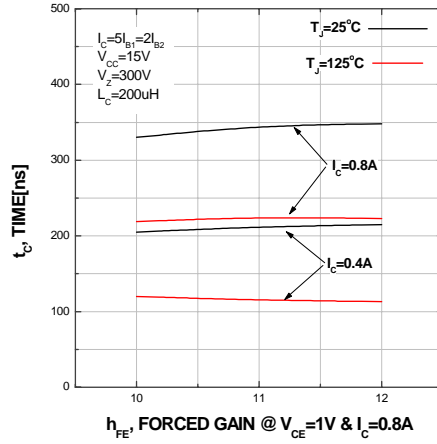


Figure 20. Inductive Switching Time, t_C

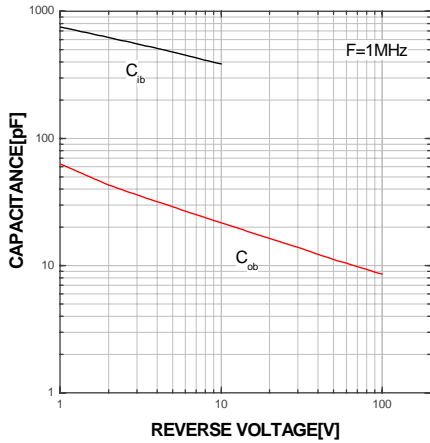


Figure 21. Capacitance

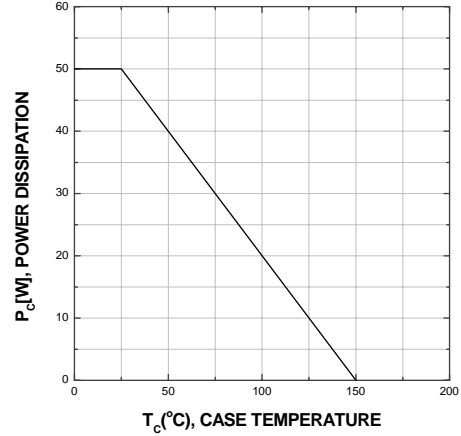


Figure 22. Power Derating



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